

**COPY**

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U.S. Department of Commerce, Patent and Trademark		Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		SNDK.211US0 (formerly M-10311 US)	09793,370
		Applicants	101804,770
(Use several sheets if necessary)		Geoffrey Gongwer and Daniel Guterman	
		Filing Date	Group
		February 26, 2001 - March 19, 2004	2825

**U.S. Patent Documents**

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>JHM</i>	1	4,628,487	Dec. 9, 1986	Smayling	—	—	
<i>JHM</i>	2	5,422,842	Jun. 6, 1995	Cerneia et al.	—	—	
<i>JHM</i>	3	5,557,567	Sep. 17, 1996	Bergemont et al.	—	—	
<i>JHM</i>	4	5,796,652	Aug. 18, 1998	Takeshima et al.	—	—	
<i>JHM</i>	5	6,014,330	Jan. 11, 2000	Endoh et al.	—	—	
<i>JHM</i>	6	6,134,148	Oct. 17, 2000	Kawahara et al.	—	—	
<i>JHM</i>	7	6,266,270 B1	Jul. 24, 2001	Nobukata	—	—	

**U.S. Published Patent Application Documents**

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

**Foreign Patent Documents**

							Translation

**OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

<i>JHM</i>	8	Chi, Min-hwa et al., "Low-Voltage Multi-level Flash Memory: Determination of Minimum Spacing Between Multi-levels," Semiconductor Electronics, 1996, ICSE 1996 Proceedings, 1996 IEEE International Conference Penang, Malaysia, November 26, 1996, pages 1-5.
<i>JHM</i>	9	Chi, Min-hwa et al., "Multi-level Flash/EPROM Memories: New Self-convergent Programming Methods for Low-voltage Applications," Electron Devices Meeting, December 10, 1995, pp. 271-274.
<i>JHM</i>	10	Ohkawa, Masayoshi et al., "A 98mm <sup>2</sup> 3.3V 64Mb Flash Memory with FN-NOR Type 4-level Cell," IEEE International Solid-State Circuits Conference, February 8, 1996, pp. 36-37 and 413.
<i>JHM</i>	11	International Search Report in counterpart PCT application PCT/US02/05265, Dec. 3, 2002, 5pages.

Examiner *JHMabsar* Date Considered 8/15/2004

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		M-10311 US	09/793,370
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicants	10/804,770
		Gongwer et al.	
		Filing Date March 19, 2004	Group
		February 26, 2001	2825

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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gfm	AB	5,623,436	4/22/97	Sowards et al.	365	45	
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### Foreign Patent Documents

							Translation
	AN						
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	AP						

### OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AQ	
	AR	
	AS	

Examiner JW Melsas Date Considered 8/5/2004

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